UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 6,774,491 B2

Page 1 of 3

APPLICATION NO.: 09/887049 DATED

: August 10, 2004

INVENTOR(S)

: Kie Y. Ahn

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Delete the title page and substitute therefor the attached title page.

On the Title Page

Page 2 Item -56- OTHER PUBLICATIONS, please delete "V. Lehrmann," before "The Physics" and insert -- V. Lehmann--.

Delete Drawing Sheet 6 of 6 and substitute therefor Drawing Sheet 6 of 6 as shown on attached page.

In the formal drawings, sheet 6 of 6. Please see attached correct drawing sheet.

Col. 1, line 9, please delete "Continuation" after "is a" and insert -- Divisional--.

Col. 5, line 4, claim 1, please insert --suspended-- after "from and".

Col. 5, line 19, claim 1, please delete "suspend" before "between" and insert --suspended--.

Col. 5, line 19, claim 1, please delete "members-" after "terminal" and insert --members--.

Col. 6, line 10, claim 14, please insert --suspended-- after "from and".

Col. 8, line 36, claim 32, please delete "32" after "claim" and insert --31--.

This certificate supersedes the Certificate of Correction issued May, 27, 2008.

Signed and Sealed this

First Day of July, 2008

JON W. DUDAS Director of the United States Patent and Trademark Office

(12) United States Patent Ahn

US 6,774,491 B2 (10) Patent No.: Aug. 10, 2004 (45) Date of Patent:

(54)	CONDUCTIVE LINES, COAXIAL LINES,
	INTEGRATED CIRCUITRY, AND METHODS
	OF FORMING CONDUCTIVE LINES,
	COAXIAL LINES, AND INTEGRATED
	CIRCUITRY

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Notice:

Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) Appl. No.: 09/887,049

Filed: Jun. 21, 2001

Prior Publication Data (65)

US 2002/0009844 A1 Jan. 24, 2002

Related U.S. Application Data

(63)	Continuation of application No. 08/917,003, filed on Aug.
, ,	20, 1997, now Pat. No. 6,294,455.

(51)	Int, CL7	H01L 23/48; H01L 23/52
(52)	U.S. CJ	. 257/773; 257/522; 257/642;
		257/619; 438/411; 438/619
(58)		,
	257/619 , 7 73,	E23.013, 758; 438/411, 412,
	610 422	121 466 623 635 626 611.

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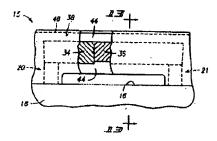
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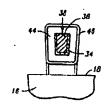
ABSTRACT

Conductive lines, such as co-axial lines, integrated circuitry incorporating such conductive lines, and methods of forming the same are described. In one aspect, a substrate having an outer surface is provided. A masking material is formed over the outer surface and subsequently patterned to form a conductive line pattern. An inner conductive layer is formed within the conductive line pattern, followed by formation of a dielectric layer thereover and an outer conductive layer over the dielectric layer. Preferred implementations include forming the inner conductive layer through electroplating, or alternatively, electroless plating techniques. Other preferred implementations include forming the dielectric layer from suitable polymer materials having desired dielectric properties. A vapor-deposited dielectric layer of Parylene is one such preferred dielectric material.

32 Claims, 6 Drawing Sheets



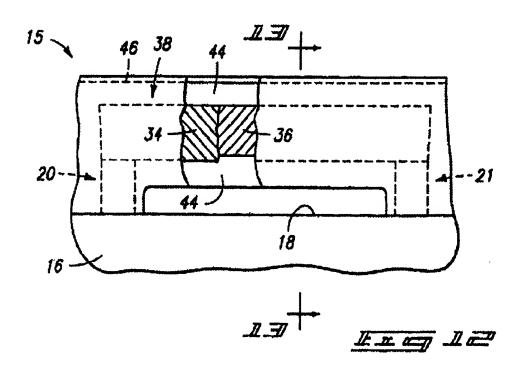
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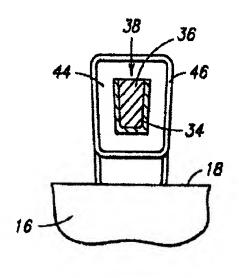


U.S. Patent

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